forming a second conductive layer on said insulating layer and said embedded conductive layer; and

forming a pixel electrode by patterning the second conductive layer, wherein said second conductive layer is light reflective.

2. (Amended) A method for producing a semiconductor device having an active matrix display device, comprising:

forming a first conductive layer;

forming an insulating layer over said first conductive layer;

forming an opening in said insulating layer to expose said first conductive layer at a bottom of said opening;

forming an oxide conductive layer by a spin coating method to cover said insulating layer and said opening;

etching or polishing said oxide conductive layer to make a state in that only said opening is filled with said oxide conductive layer; and

forming a second conductive layer on said insulating layer and said oxide conductive layer; and

forming a pixel electrode by patterning the second conductive layer, wherein said second conductive layer is light reflective.

3. (Amended) A method for producing a semiconductor device having an active matrix display device, comprising: forming an active layer of a transistor;

forming an insulating layer over said active layer;

forming an opening in said insulating layer to expose a portion of the active layer at a bottom of said opening;

forming an embedded conductive layer comprising a black colored material to cover said insulating layer and said opening wherein the embedded conductive layer contacts the active layer in the opening;

forming a transparent conductive layer on said embedded conductive layer;

patterning said transparent conductive layer to form a transparent pixel electrode.

4. (Amended) A method for producing a semiconductor device having an active matrix display device, comprising:

forming a first conductive layer;

forming an insulating layer over said first conductive layer;

forming an opening in said insulating layer to expose said first conductive layer at a bottom of said opening;

forming an oxide conductive layer by a spin coating method, to cover said insulating layer and said opening;

forming a second conductive layer on said oxide conductive layer;

patterning said second conductive layer to form a pixel electrode wherein said second conductive layer is light reflective, and

etching said oxide conductive layer by using said second conductive layer as a mask in a self alignment manner.

14. (Amended) A method for producing a semiconductor device having an active matrix display device, comprising:

forming a first conductive layer;

forming an insulating layer over said first conductive layer;

forming an opening in said insulating layer to expose said first conductive layer at a bottom of said opening;

forming a second conductive layer comprising a conductive oxide to cover said insulating layer and said opening;

polishing said second conductive layer by employing a chemical mechanical polishing; and

forming a third conductive layer on said insulating layer and said second conductive layer,

wherein said third conductive layer is reflective.

15. (Amended) A method for producing a semiconductor device having an active matrix display device, comprising:

forming an active layer of a transistor;

forming an insulating layer over the active layer;

forming an opening in said insulating layer to expose a portion of the active layer at a bottom of said opening;

forming a black colored conductive layer to cover said insulating layer and said opening;

polishing said black colored conductive layer by employing a chemical mechanical polishing; and

forming a second conductive layer on said insulating layer and said oxide conductive layer, wherein said second conductive layer is transparent; and

forming a pixel electrode by patterning said second conductive layer.

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28. (Amended) A method for producing a semiconductor device having an active matrix display device, comprising:

forming a first conductive layer;

forming an insulating layer comprising an organic resin over said first conductive layer;

forming an opening in said insulating layer to expose said first conductive layer at a bottom of said opening;

forming an embedded conductive layer comprising an organic resin to cover said insulating layer and said opening;

removing a portion of said embedded conductive layer to expose a portion of the insulating layer; and

forming a second conductive layer on said insulating layer and said embedded conductive layer; and

forming a pixel electrode by patterning the second conductive layer.

29. (Amended) A method for producing a semiconductor device having an active matrix display device, comprising:

forming a first conductive layer;

forming an insulating layer over said first conductive layer;

forming an opening in said insulating layer to expose said first conductive layer at a bottom of said opening;

filling said opening with a second conductive layer comprising a conductive oxide to cover said insulating layer and said opening;

forming a reflective pixel electrode on the insulating layer, wherein said reflective pixel electrode is electrically connected to the first conductive layer through the second conductive layer.